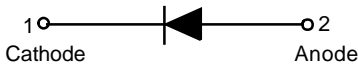
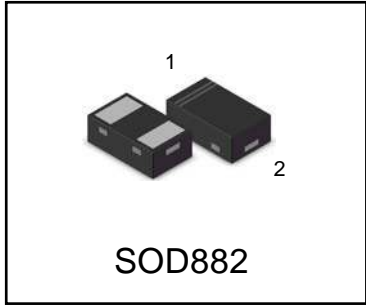


BAS70BS

S-BAS70BS

Schottky barrier diode



1. FEATURES

- Low forward current
- High breakdown voltage
- Guard ring protected
- Low diode capacitance.
- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.

2. APPLICATIONS

- Ultra high-speed switching
- Voltage clamping
- Protection circuits.

3. DEVICE MARKING AND RESISTOR VALUES

Device	Marking	Shipping
BAS70BS	R	10000/Tape&Reel

4. MAXIMUM RATINGS(Ta = 25°C)

Parameter	Symbol	Limits	Unit
Continuous reverse voltage	VR	70	V
Continuous forward current	IF	70	mA
Repetitive Peak forward surge current(tp ≤1s,δ≤0.5)	IFRM	70	mA
Non-repetitive peak forward current (tp <10ms)	IFSM	100	mA
Storage temperature	Tstg	-65~+125	°C
Junction temperature	Tj	125	°C

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Thermal resistance from junction to ambient (Note 1)	RθJA	833	°C/W

1. FR-4 Minimum Pad.



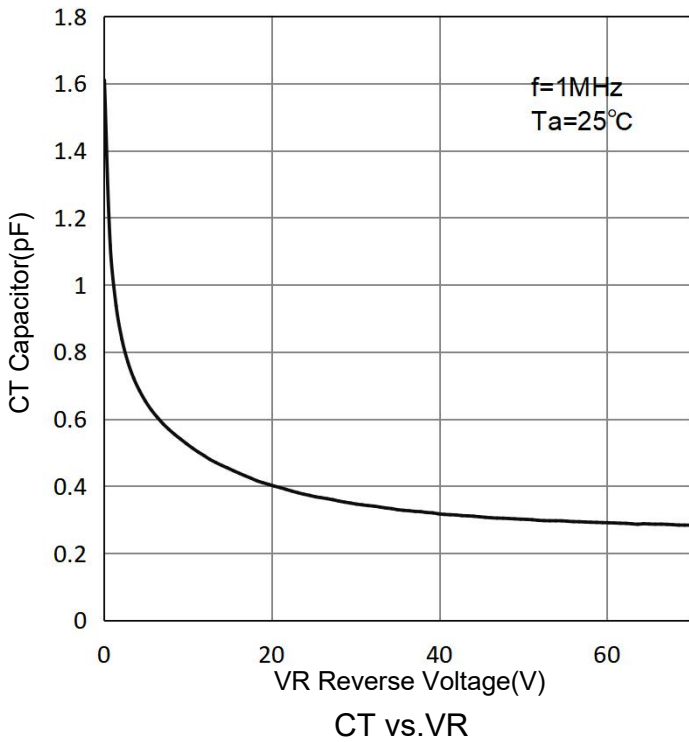
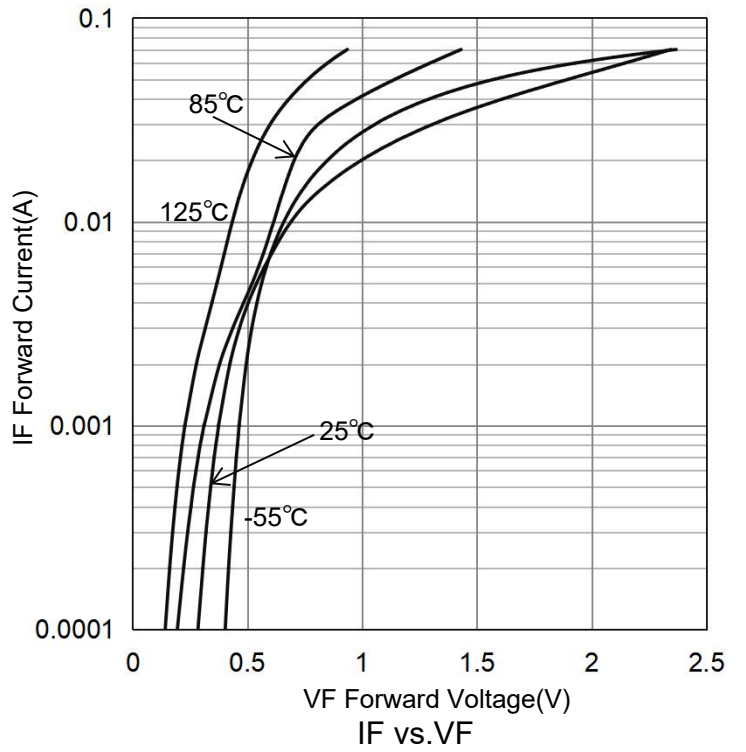
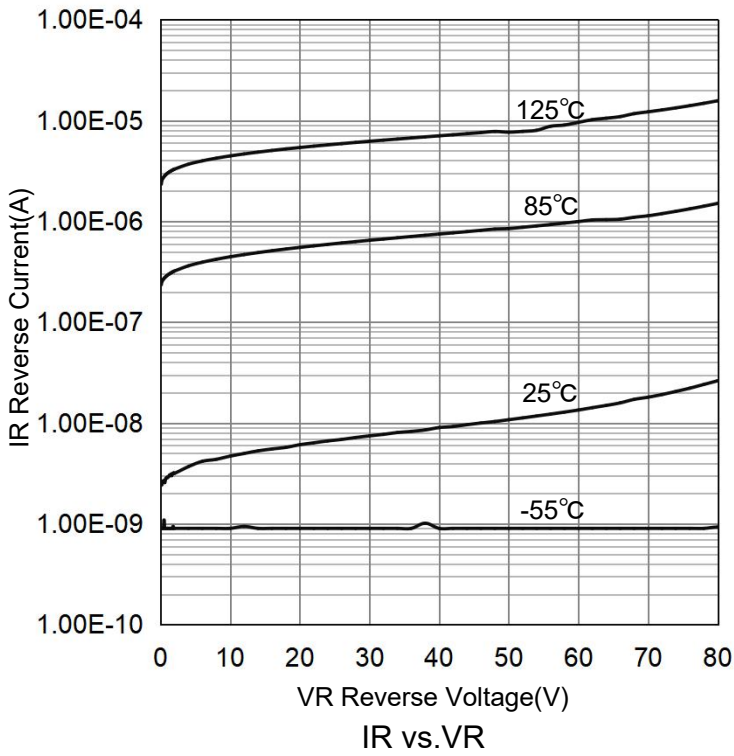
6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	Symbol	Limits	Unit
Forward voltage (IF =1mA)	VF	410	mV
(IF =10mA)		750	mV
(IF =15mA)		1	V
Reverse current(Note 2) (VR=50V)	IR	100	nA
(VR=70V)		10	μA
Charge carrier life time (IF =5mA)	τ	100	pS
Diode capacitance (f=1MHz,VR =0)	Cd	2	pF

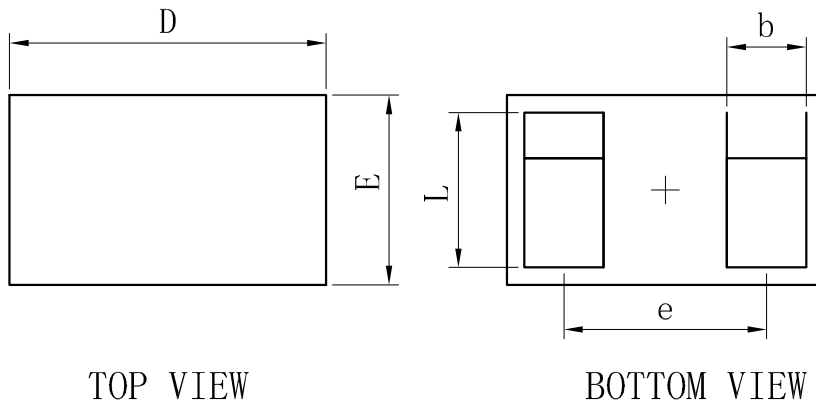
2.Pulse test:tp =300μs,δ=0.02.



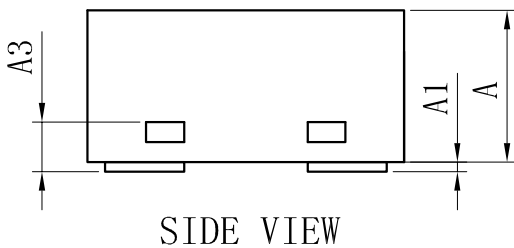
7. ELECTRICAL CHARACTERISTICS CURVES



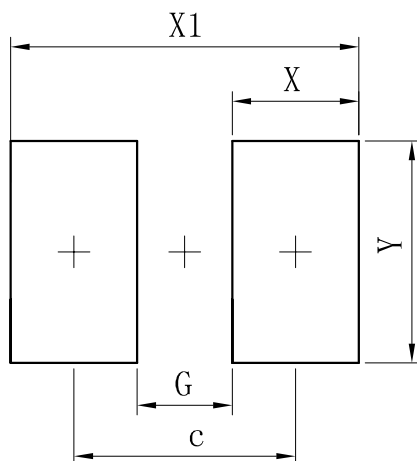
8. OUTLINE AND DIMENSIONS



SOD882			
Dim	Min	Typ	Max
D	0.95	1.00	1.05
E	0.55	0.60	0.65
e	-	0.64	-
L	0.44	0.49	0.54
b	0.20	0.25	0.30
A	0.43	0.48	0.53
A1	0	-	0.05
A3	0.127REF.		
All Dimensions in mm			



9. SOLDERING FOOTPRINT



Dimensions	(mm)
c	0.70
G	0.30
X	0.40
X1	1.10
Y	0.70

